

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTORNEY DOCKET NO. 047071-0109

Applicant: Harry A. ATWATER et al.
Title: WAFER BONDED EPITAXIAL TEMPLATES FOR SILICON
HETEROSTRUCTURES
Appl. No.: 10/784,586
Filing Date: 02/23/2004
Examiner: Unassigned
Art Unit: 1764

INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR §1.56

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Submitted herewith on Form PTO/SB/08 a listing of the documents cited by or submitted to the U.S. PTO in parent application Serial No. 10/125,133, filed April 17, 2002. As provided in 37 CFR §1.98(d), copies of the documents are not being provided since they were previously submitted to the United States Patent & Trademark Office in the above-identified parent application.

The submission of any document herewith, which is not a statutory bar, is not intended as an admission that such document constitutes prior art against the claims of the present application or that such document is considered material to patentability as defined in 37 CFR §1.56(b). Applicants do not waive any rights to take any action which would be appropriate to antedate or otherwise remove as a competent reference any document which is determined to be a *prima facie* art reference against the claims of the present application.

TIMING OF THE DISCLOSURE

The listed documents are being submitted in compliance with 37 CFR §1.97(b), before the mailing date of the first Office Action on the merits.

RELEVANCE OF EACH DOCUMENT

The relevance of the documents is explained in the parent application.


Applicants respectfully request that any listed document be considered by the Examiner and be made of record in the present application and that an initialed copy of Form PTO/SB/08 be returned in accordance with MPEP §609.

The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 CFR §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 19-0741. Should no proper payment be enclosed herewith, as by a check being in the wrong amount, unsigned, post-dated, otherwise improper or informal or even entirely missing, the Commissioner is authorized to charge the unpaid amount to Deposit Account No. 19-0741.

Respectfully submitted,

Date January 7, 2005

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By 
Leon Radomsky
Attorney for Applicant
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Date Submitted: 1/7/05

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Sheet 1 of 7

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| | | | | Application Number | 10/784,586 |
| | | | | Filing Date | 02/23/2004 |
| | | | | First Named Inventor | Harry A. ATWATER et al. |
| | | | | Group Art Unit | 1764 |
| | | | | Examiner Name | Unassigned |
| | | | | Attorney Docket Number | 047071-0109 |
| Sheet | 6 | of | 7 | | |

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